L Number	Hits	Search Text	DB	Time stamp
157	16	("3629088" | "4277320" | "4300989" | "4636400" | "4715937" | "4917843" | "5376593" | "5445999" | "5618755" | "5747357" | "5907792" | "5913149" | "5989338" | "6077754" | "6087229" | "6136388").PN.	USPAT	2004/03/05 09:41
-	6	(("6077257") or ("6077751") or ("6303520")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 13:29
-	69	kick adj out adj mechanism	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/04 13:40
-	61	(kick adj out adj mechanism) and @ad<=19990503	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/04 13:40
-	4	5151766.URPN.	USPAT	2002/06/04 14:29
-	9	("3888701" | "3933527" | "4056408" | "4115798" | "4240844" | "4249962" | "4278475" | "4406709" | "4987087").PN.	USPAT	2002/06/04 14:30
-	5887	((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or (257/219) or (257/609) or (257/617) or (257/649)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:29
-	5109	(((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or (257/219) or (257/609) or (257/617) or (257/649)).CCLS.) and @ad<=19990503	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/04 15:05
-	1867	(control controlling controlled controls) same (defect vancancy) same (gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/04 15:09
-	168	((control controlling controlled controls) same (defect vancancy) same (gas)) and ((silicon adj oxynitride) (silicon adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:16
-	8	("4705591" | "4755865" | "4766477" | "4772927" | "4968384" | "4998150" | "5463978" | "5683934").PN.	USPAT	2002/06/04 17:13
-	4	(boron b) and (defect adj enhanced adj diffusion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:23
-	4	(boron b arsenic as antimony sb indium in) and (defect adj enhanced adj diffusion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:26
-	4	(boron b arsenic as antimony sb indium in) and ((defect trasient) adj enhanced adj diffusion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:28

-	5436	(boron b arsenic as antimony sb indium in) and (((defect trasient) adj enhanced adj diffusion) gettering)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:29
-	6409	((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or (257/219) or (257/609) or (257/617) or (257/649) or (438/143) or (438/476) or (438/472) or (438/473)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:30
-	5557	(((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or (257/219) or (257/609) or (257/617) or (257/649) or (438/143) or (438/476) or (438/472) or (438/473)).CCLS.) and @ad<=19990503	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:31
-	1208	((((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or (257/219) or (257/609) or (257/617) or (257/649) or (438/143) or (438/476) or (438/472) or (438/473)).CCLS.) and @ad<=19990503) and ((silicon adj oxynitride) siono sion (silicon adj nitride) sin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:32
-	328	(((((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or (257/219) or (257/609) or (257/617) or (257/649) or (438/143) or (438/476) or (438/472) or (438/473)).CCLS.) and @ad<=19990503) and ((silicon adj oxynitride) siono sion (silicon adj nitride) sin)) and (control same (gas temperature thermal concentration pressure))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:49
-	150	((((((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or (257/219) or (257/609) or (257/617) or (257/649) or (438/143) or (438/476) or (438/472) or (438/473)).CCLS.) and @ad<=19990503) and ((silicon adj oxynitride) siono sion (silicon adj nitride) sin)) and (control same (gas temperature thermal concentration pressure))) and (defect vacancy vacant) and (creation generation generate formation forming formed creates created)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:01
-	986	(generating creating) adj defect	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:02
-	105	((generating creating) adj defect) and (semiconductor with material)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:07
-	83	(((generating creating) adj defect) and (semiconductor with material)) and @ad<=19990503	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:08

-	21	(((generating creating) adj defect) and (semiconductor with material)) and @ad<=19990503) and (silicon adj (nitride oxynitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:08
-	423	((control controlling controlled controls) same (defect vancancy) same (temperature (partial adj pressure)) and ((silicon adj oxynitride) (silicon adj nitride)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:20
-	319	(((control controlling controlled controls) same (defect vancancy) same (temperature (partial adj pressure)) and ((silicon adj oxynitride) (silicon adj nitride)))) and @ad<=19990503	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:20
-	273	((((control controlling controlled controls) same (defect vancancy) same (temperature (partial adj pressure)) and ((silicon adj oxynitride) (silicon adj nitride)))) and @ad<=19990503) and thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:21
-	176	(((((control controlling controlled controls) same (defect vancancy) same (temperature (partial adj pressure)) and ((silicon adj oxynitride) (silicon adj nitride)))) and @ad<=19990503) and thickness) and concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:21
-	34	((((((control controlling controlled controls) same (defect vancancy) same (temperature (partial adj pressure)) and ((silicon adj oxynitride) (silicon adj nitride)))) and @ad<=19990503) and thickness) and concentration) and (thermal with stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:22
-	33	(lattice with defects with control$3) and 438/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 10:35
-	11	((lattice with defects with control$3) and 438/$.ccls.) and atmosphere	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 10:36
-	0	(deffect adj enhanced adj diffusion) and (((438/$) (257/$)).ccls.)	USPAT	2002/11/30 11:36
-	4	(defect adj enhanced adj diffusion) and (((438/$) (257/$)).ccls.)	USPAT	2002/11/30 13:00
-	6	("5216271" | "5285088" | "5432366" | "5569624" | "5955745" | "6048756").PN.	USPAT	2002/11/30 12:38
-	2	(defect adj enhanced adj diffusion) and silicon adj (nitride oxynitride)	USPAT	2002/11/30 13:00
-	2	(defect adj enhanced adj diffusion) and (silicon adj (nitride oxynitride))	USPAT	2002/11/30 13:11
-	8	("4705591" | "4755865" | "4766477" | "4772927" | "4968384" | "4998150" | "5463978" | "5683934").PN.	USPAT	2002/11/30 13:01
-	0	((defect adj enhanced adj diffusion) and (silicon adj (nitride oxynitride))) and (outdiffusion (out adj diffusion))	USPAT	2002/11/30 13:09
-	91	((defect transient) with enhanced with diffusion) and (silicon adj (nitride (oxy adj nitride) oxynitride))	USPAT	2002/11/30 13:12
-	53	(((defect transient) with enhanced with diffusion) and (silicon adj (nitride (oxy adj nitride) oxynitride))) and @ad<=19990503	USPAT	2002/11/30 13:13
-	32	((((defect transient) with enhanced with diffusion) and (silicon adj (nitride (oxy adj nitride) oxynitride))) and @ad<=19990503) and control	USPAT	2002/11/30 13:13

-	3	(((((defect transient) with enhanced with diffusion) and (silicon adj (nitride (oxy adj nitride) oxynitride))) and @ad<=19990503) and control$4) and (outdiffusion (out adj diffusion) outdiffused)	USPAT	2002/11/30 13:14
-	14	("4841346" | "5478763" | "5500379" | "5543337" | "5578510" | "5851886" | "5874329" | "5893740" | "6010952" | "6020231" | "6020244" | "6025232" | "6030875" | "6051860").PN.	USPAT	2002/11/30 13:16
-	43	((((defect transient) with enhanced with diffusion) and (silicon adj (nitride (oxy adj nitride) oxynitride))) and @ad<=19990503) and control$4	USPAT	2002/11/30 13:35
-	1	((((defect transient) with enhanced with diffusion) and (silicon adj (nitride (oxy adj nitride) oxynitride))) and @ad<=19990503) and control$4 with gas$4	USPAT	2002/11/30 13:39
-	184	lerch.inv.	USPAT	2002/11/30 13:39
-	1	lerch.inv. and rtp.as.	USPAT	2002/11/30 13:39
-	1	lerch.inv. and steag.as.	USPAT	2002/11/30 13:39
-	299	((438/413) or (438/419)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/30 13:57
-	101	(((438/413) or (438/419)).CCLS.) and silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/30 14:12
-	0	((((438/413) or (438/419)).CCLS.) and silicon adj nitride) and outdiffusion with prevent$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/30 13:58
-	2	((((438/413) or (438/419)).CCLS.) and silicon adj nitride) and (out with diffusion) with prevent$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/30 13:59
-	15	3929528.URPN.	USPAT	2002/11/30 14:00
-	0	(((438/413) or (438/419)).CCLS.) and (silicon adj nitride) with (outdiffusion (out adj diffusion))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/30 14:13
-	47	438/$.ccls. and (silicon adj nitride) with (outdiffusion (out adj diffusion))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/30 14:13
-	36	(438/$.ccls. and (silicon adj nitride) with (outdiffusion (out adj diffusion))) and @ad<=19990503	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/30 14:14
-	6	(("5387548") or ("5967794") or ("6319779")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/30 16:02

-	6293	((438/5) or (438/289) or (438/290) or (438/301) or (438/307) or (438/471) or (438/522) or (438/530) or (438/916) or (438/920) or (438/for.445) or (257/55) or (257/63) or (257/191) or (257/219) or (257/609) or (257/617) or (257/649) or (438/795) or (438/472) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/796) or (438/797) or (438/798) or (438/799) or (438/143) or (438/476) or (438/472) or (438/473) or (438/477)).CCLS.	USPAT; US-PGPUB	2003/07/08 09:05
-	2989	(((438/5) or (438/289) or (438/290) or (438/301) or (438/307) or (438/471) or (438/522) or (438/530) or (438/916) or (438/920) or (438/for.445) or (257/55) or (257/63) or (257/191) or (257/219) or (257/609) or (257/617) or (257/649) or (438/795) or (438/472) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/796) or (438/797) or (438/798) or (438/799) or (438/143) or (438/476) or (438/472) or (438/473) or (438/477)).CCLS.) and control	USPAT; US-PGPUB	2003/07/08 09:06
-	391	(((438/5) or (438/289) or (438/290) or (438/301) or (438/307) or (438/471) or (438/522) or (438/530) or (438/916) or (438/920) or (438/for.445) or (257/55) or (257/63) or (257/191) or (257/219) or (257/609) or (257/617) or (257/649) or (438/795) or (438/472) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/796) or (438/797) or (438/798) or (438/799) or (438/143) or (438/476) or (438/472) or (438/473) or (438/477)).CCLS.) and control$4 with (concentration pressure temperature) with (dopant impurity doping)	USPAT; US-PGPUB	2003/07/08 11:25
-	77	((((438/5) or (438/289) or (438/290) or (438/301) or (438/307) or (438/471) or (438/522) or (438/530) or (438/916) or (438/920) or (438/for.445) or (257/55) or (257/63) or (257/191) or (257/219) or (257/609) or (257/617) or (257/649) or (438/795) or (438/472) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/796) or (438/797) or (438/798) or (438/799) or (438/143) or (438/476) or (438/472) or (438/473) or (438/477)).CCLS.) and control$4 with (concentration pressure temperature) with (dopant impurity doping)) and gas with atmosphere	USPAT; US-PGPUB	2003/07/08 09:09
-	17	(((438/5) or (438/289) or (438/290) or (438/301) or (438/307) or (438/471) or (438/522) or (438/530) or (438/916) or (438/920) or (438/for.445) or (257/55) or (257/63) or (257/191) or (257/219) or (257/609) or (257/617) or (257/649) or (438/795) or (438/472) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/796) or (438/797) or (438/798) or (438/799) or (438/143) or (438/476) or (438/472) or (438/473) or (438/477)).CCLS.) and control$4 with (outdiffusion ("out diffusion"))	USPAT; US-PGPUB	2003/07/08 11:25
-	7383	control$4 with (concentration pressure temperature) with (dopant impurity doping)	USPAT; US-PGPUB	2003/07/08 11:26
-	201	control$4 with (outdiffusion ("out diffusion"))	USPAT; US-PGPUB	2003/07/08 11:26
-	57	(control$4 with (concentration pressure temperature) with (dopant impurity doping)) and (control$4 with (outdiffusion ("out diffusion")))	USPAT; US-PGPUB	2003/07/08 13:37

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-	8	((((438/5) or (438/289) or (438/290) or (438/301) or (438/307) or (438/471) or (438/522) or (438/530) or (438/916) or (438/920) or (438/for.445) or (257/55) or (257/63) or (257/191) or (257/219) or (257/609) or (257/617) or (257/649) or (438/795) or (438/472) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/796) or (438/797) or (438/798) or (438/799) or (438/143) or (438/476) or (438/472) or (438/473) or (438/477)).CCLS.) and control$4 with (outdiffusion ("out diffusion"))) and ((control$4 with (concentration pressure temperature) with (dopant impurity doping)) and (control$4 with (outdiffusion ("out diffusion"))))	USPAT; US-PGPUB	2003/07/08 11:26
-	7	5569615.URPN.	USPAT	2003/07/08 13:19
-	6	("4780424" | "4861730" | "5114876" | "5158903" | "5180690" | "5569615").PN.	USPAT	2003/07/08 13:22
-	57	(control$4 with (concentration pressure temperature) with (dopant impurity doping)) and (control$4 with (outdiffusion ("out diffusion")))	USPAT; US-PGPUB	2003/07/08 13:39
-	7241	dop$3 with profile	USPAT; US-PGPUB	2004/02/27 14:07
-	912	thermal with process with (ammonia "nh.sub.3" "no.sub.2")	USPAT; US-PGPUB	2004/02/27 14:07
-	17	(dop$3 with profile) and (thermal with process with (ammonia "nh.sub.3" "no.sub.2"))	USPAT; US-PGPUB	2004/02/27 14:08
-	321	forming with silicon with (nitride or oxynitride) with doped with substrate	USPAT; US-PGPUB	2004/03/01 13:32
-	10	forming with silicon with (nitride or oxynitride) with doped with substrate with thickness with ("2" or "4")	USPAT; US-PGPUB	2004/03/01 13:36
-	24	(forming with silicon with (nitride or oxynitride) with doped with substrate) and thickness with ("2 nm" or "20 angstroms" or "4 nm" or "40 angstroms")	USPAT; US-PGPUB	2004/03/01 13:37
-	16	("3629088" | "4277320" | "4300989" | "4636400" | "4715937" | "4917843" | "5376593" | "5445999" | "5618755" | "5747357" | "5907792" | "5913149" | "5989338" | "6077754" | "6087229" | "6136388").PN.	USPAT	2004/03/01 15:20
-	16	("3629088" | "4277320" | "4300989" | "4636400" | "4715937" | "4917843" | "5376593" | "5445999" | "5618755" | "5747357" | "5907792" | "5913149" | "5989338" | "6077754" | "6087229" | "6136388").PN.	USPAT	2004/03/04 10:51
-	18	6087229.URPN.	USPAT	2004/03/04 11:38
-	11	("4621277" | "4913929" | "5258333" | "5422291" | "5464783" | "5834351" | "5837598" | "5888870" | "5904523" | "5960289" | "5969397").PN.	USPAT	2004/03/04 11:43
-	23	5422291.URPN.	USPAT	2004/03/04 11:52
-	11	5600166.URPN.	USPAT	2004/03/04 11:55
-	18	6087229.URPN.	USPAT	2004/03/04 11:55